

SMALL SIGNAL SCHOTTKY DIODE

VOLTAGE RANGE: 50 V
CURRENT: 0.2 A

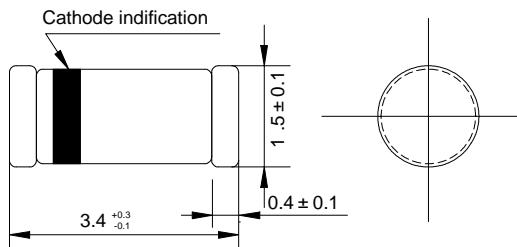
FEATURES

- ◇ For general purpose applications
- ◇ This diode features very low turn-on voltage and fast switching. These devices are protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges

MECHANICAL DATA

- ◇ Case: JEDEC mini-melf, glass case
- ◇ Polarity: Color band denotes cathode end
- ◇ Weight: Approx. 0.031 grams

Mini-melf



Dimensions in millimeters

ABSOLUTE RATINGS

	Symbols	Value	UNITS
Continuous reverse voltage	V_R	50	V
Forward continuous current @ $T_A=25^\circ C$	I_F	200 ¹⁾	mA
Peak forward current @ $T_A=25^\circ C$	I_{FM}	500 ¹⁾	mA
Surge forward current @ $t_p < 1s, T_A=25^\circ C$	I_{FSM}	5 ¹⁾	A
Power dissipation @ $T_A=65^\circ C$	P_{tot}	200 ¹⁾	mW
Junction temperature	T_J	125	°C
Ambient operating temperature range	T_A	-55 ---- 125	°C
Storage temperature range	T_{STG}	-55 ---- 150	°C

1) Valid provided that leads at a distance of 4mm from case are kept at ambient temperature

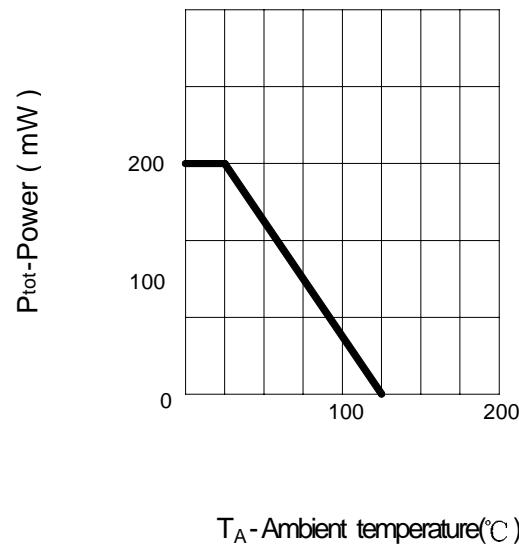
ELECTRICAL CHARACTERISTICS

	Symbols	Min.	Typ.	Max.	UNITS
Reverse breakdown voltage	V_R	50.0			V
Forward voltage Pulse test $t_p < 300 \mu s, \delta < 2\%$ @ $I_F=0.1mA$ @ $I_F=1mA$ @ $I_F=10mA$ @ $I_F=30mA$ @ $I_F=100mA$	V_F			0.30 0.38 0.45 0.60 0.90	V
Leakage current $V_R=40V$	I_R			5.0	μA
Diode capacitance at $V_R=1V, f=1MHz$	C_d			8	pF
Reverse recovery time @ $I_F=10mA, I_R=10mA, I_L=1mA$	t_{rr}			5	ns
Thermal resistance junction to ambient	$R_{\theta JA}$			430 ¹⁾	°C/W

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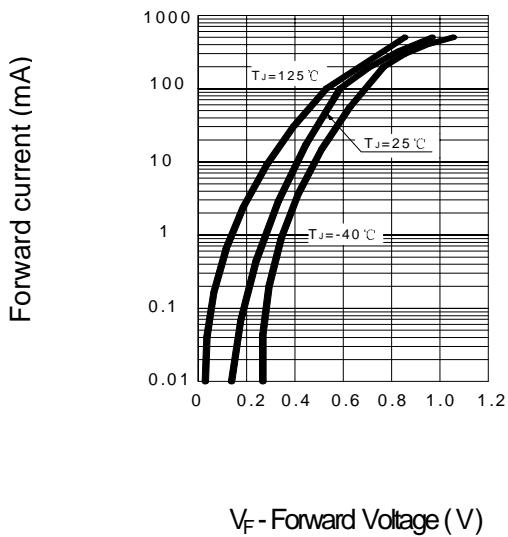
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FIG.1 – ADMISSIBLE POWER DISSIPATION VS. AMBIENT TEMPERATURE



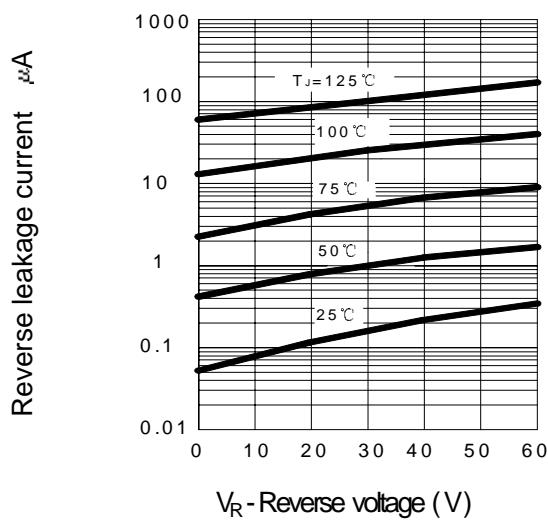
T_A - Ambient temperature (°C)

FIG. 2-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS



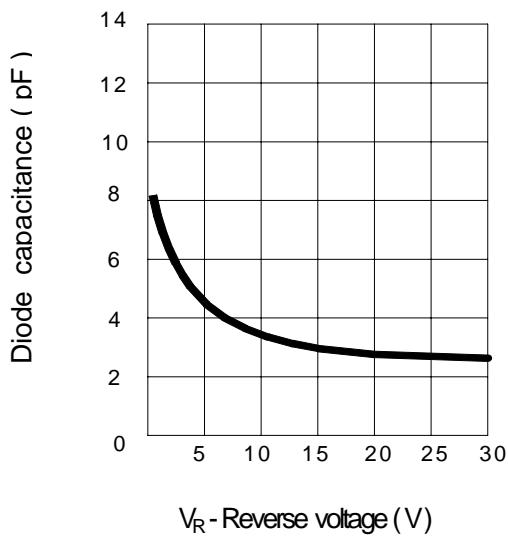
V_F - Forward Voltage (V)

FIG. 3 – TYPICAL REVERSE CHARACTERISTICS



V_R - Reverse voltage (V)

FIG.4 – TYPICAL JUNCTION CAPACITANCE



V_R - Reverse voltage (V)